

# **BUK7E13-60E**

# N-channel TrenchMOS standard level FET 11 September 2012

**Product data sheet** 

#### **Product profile** 1.

#### 1.1 General description

Standard level N-channel MOSFET in a SOT226 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

## 1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

## 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	58	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	96	W
Static characte	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11		-	9.6	13	mΩ
Dynamic characteristics							
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V; Fig. 13; Fig. 14		-	6.9	-	nC



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# 2. Pinning information

**Table 2.** Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain		
3	S	source		G
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			I2PAK (SOT226)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK7E13-60E	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226			

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	60	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	60	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-20	20	V
$I_D$	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>		-	58	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>		-	41	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 4		-	234	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	96	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	58	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	234	Α

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Symbol	Parameter	Conditions		Min	Max	Unit
Avalanche rug	igedness					
E <sub>DS(AL)</sub> S	non-repetitive drain-source avalanche energy	$I_D$ = 58 A; $V_{sup} \le$ 60 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 60 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[2][3]	-	37	mJ

- [1]
- Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175  $^{\circ}\text{C}.$
- Refer to application note AN10273 for further information.

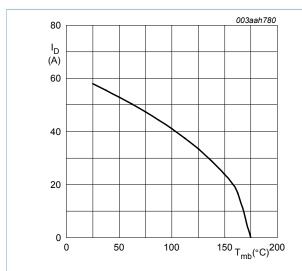


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 10V$$

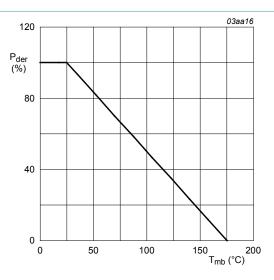
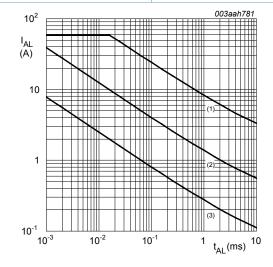


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \,\%$$



Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) 
$$T_{j \ (init)} = 25^{\circ}C$$
; (2)  $T_{j \ (init)} = 150^{\circ}C$ ; (3) Repetitive Avalanche

BUK7E13-60E

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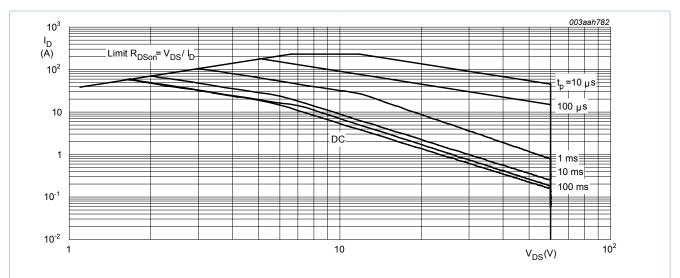


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25$ °C;  $I_{DM}$  is a single pulse

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	1.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	65	-	K/W

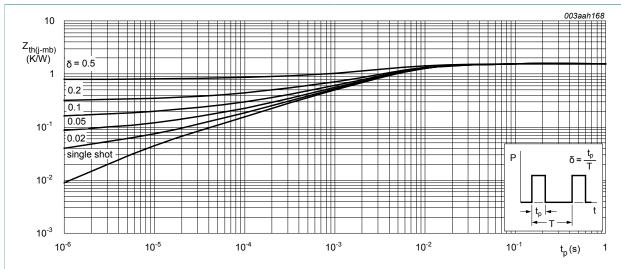


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

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# 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; Fig. 9	1	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 9	-	-	4.5	V
I <sub>DSS</sub> di	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.025	1	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub> drain-source or resistance	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 25 °C; Fig. 11	-	9.6	13	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	-	28.2	mΩ
Dynamic ch	naracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	Fig. 12: Fig. 14	-	22.9	-	nC
$Q_{GS}$	gate-source charge		-	5	-	nC
$Q_{GD}$	gate-drain charge		-	6.9	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	1298	1730	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	197	237	pF
C <sub>rss</sub>	reverse transfer capacitance		-	122	162	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 45 V; $R_L$ = 3 $\Omega$ ; $V_{GS}$ = 10 V;	-	10.8	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	9.2	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	21.9	-	ns
t <sub>f</sub>	fall time		-	9.8	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of mounting base to centre of die ; $T_j$ = 25 °C	-	2.5	-	nH
		T <sub>j</sub> = 25 °C; from drain lead 6mm from package to centre of die	-	4.5	-	nH
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad ; T <sub>i</sub> = 25 °C	-	7.5	-	nH

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain diode							
$V_{SD}$	source-drain voltage	$I_S = 20 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$		-	0.84	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 15 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	21.3	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V		-	18.1	-	nC

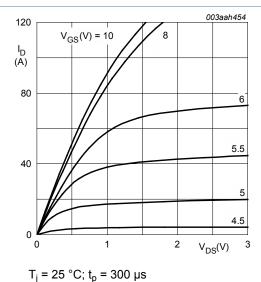


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

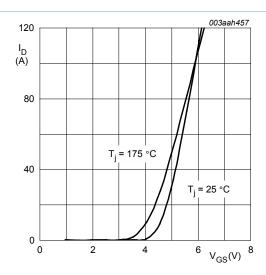


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



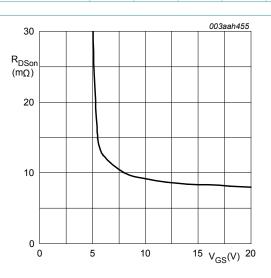


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 15A$$

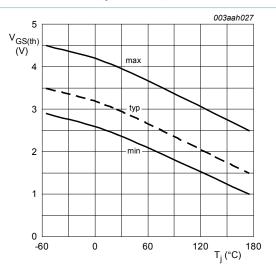


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

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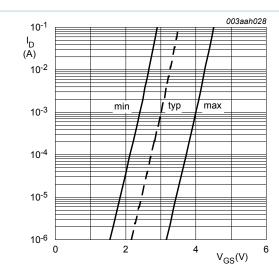


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

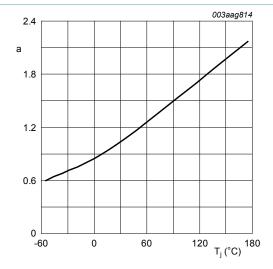
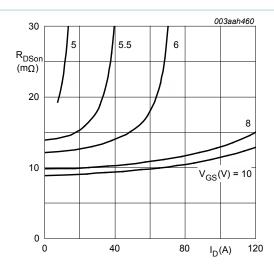


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$\mathbf{a} = \frac{R_{DSon}}{R_{DSon(25 \, \text{C})}}$$



 $T_j = 25 \, ^{\circ}C; t_p = 300 \, \mu s$ 

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

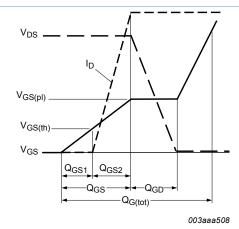


Fig. 13. Gate charge waveform definitions

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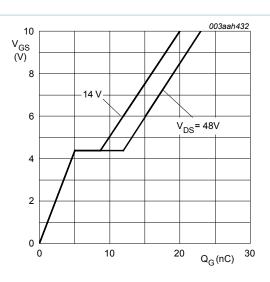


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C;  $I_D = 15A$ 

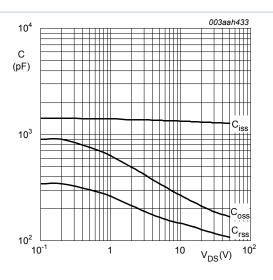


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

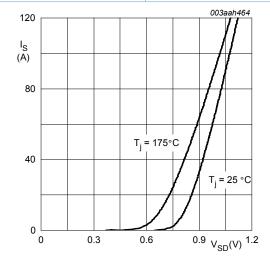


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

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# 7. Package outline

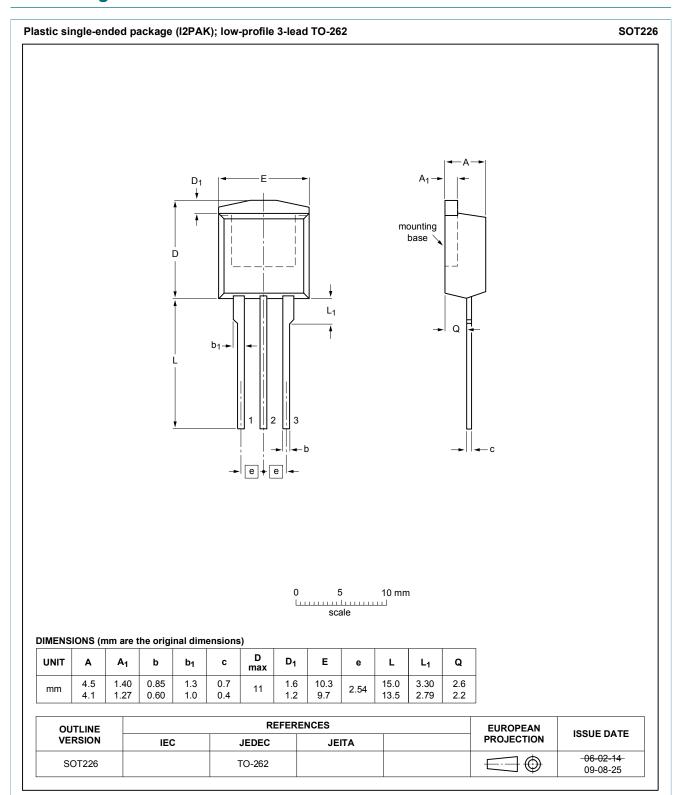


Fig. 17. Package outline I2PAK (SOT226)

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